



AMENDMENT TO CLAIMS

1. (Currently amended) A pattern formation method comprising the steps of:
forming a resist film made from a resist material including a material ~~[[of]]~~ for absorbing moisture;
performing pattern exposure by selectively irradiating said resist film with exposing light while supplying immersion solution onto said resist film; and
forming a resist pattern by developing said resist film after the pattern exposure,
wherein said material for absorbing moisture is hygroscopic compound or a rare earth compound.
2. (Cancelled)
3. (Currently amended) The pattern formation method of Claim ~~[[2]]~~ 1,
wherein said hygroscopic compound is ethylene glycol, polyethylene glycol, glycerin or *N*-methyl-2-pyrrolidone.
4. (Withdrawn-currently amended) The pattern formation method of Claim ~~[[2]]~~ 1,
wherein said rare earth compound is an oxide, a chloride, a sulfate, a nitrate, a hydroxide, an acetate, an octylate, yttrium oxide, neodymium oxide, cerium oxide, lanthanum oxide, scandium oxide, cerium chloride, ceric sulfate, ammonium ceric sulfate, cerium nitrate, ammonium cerium nitrate, lanthanum nitrate, cerium hydroxide, cerium acetate or cerium octylate.

5. (Withdrawn) The pattern formation method of Claim 1,
wherein said exposing light is KrF excimer laser, ArF excimer laser, F₂ laser, KrAr laser
or Ar₂ laser.

6-18. (Canceled)